

FULL-SIZE DIP HIGH-FREQUENCY CRYSTAL OSCILLATOR

SG-51 series

HALF-SIZE DIP HIGH-FREQUENCY CRYSTAL OSCILLATOR

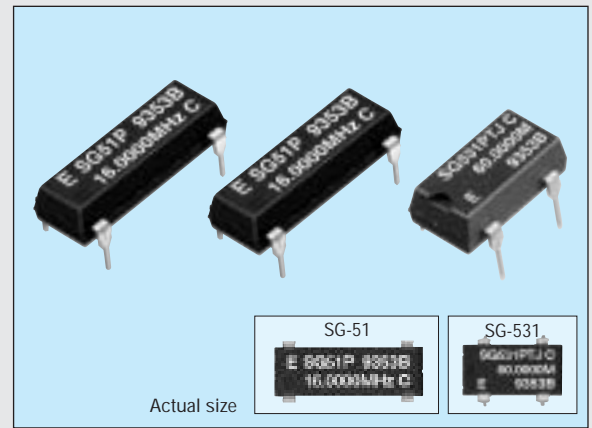
SG-531 series

Product number (please refer to page 1)

Q32510xxxxxx00

Q32531xxxxxx00

- Pin compatible with full-size metal can. (SG-51 series)
- Pin compatible with half-size metal can. (SG-531 series)
- Cylindrical AT-cut crystal unit builtin, thus assuring high reliability.
- Use of CMOS IC enables reduction of current consumption.



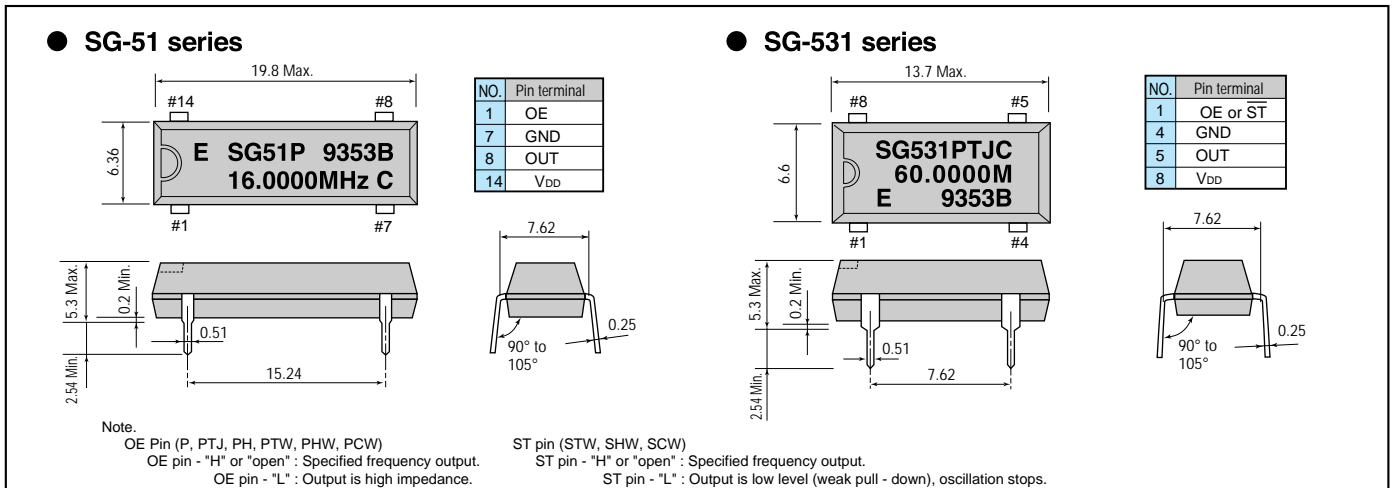
Specifications (characteristics)

Item	Symbol	Specifications			Remarks
		SG-51P/531P	SG-51PTJ/531PTJ	SG-51PH/531PH	
Output frequency range	f_0	1.0250 MHz to 26.0000 MHz	26.0001 MHz to 66.6667 MHz		Refer to page 31. "Frequency range"
Power source voltage	Max. supply voltage	V_{DD-GND}	-0.3 V to +7.0 V	-0.5 V to +7.0 V	
	Operating voltage	V_{DD}	5.0 V \pm 0.5 V		
Temperature range	Storage temperature	T_{STG}	-55 °C to +125 °C		Stored as bare product after unpacking
	Operating temperature	T_{OPR}	-20 °C to +70 °C (-40 °C to +85 °C)		Refer to page 31. "Frequency range"
Frequency stability	$\Delta f/f_0$		B: $\pm 50 \times 10^{-6}$ C: $\pm 100 \times 10^{-6}$		B type is possible up to 55.0 MHz
Current consumption	I_{OP}	23 mA Max.	35 mA Max.		No load condition
Output disable current	I_{OE}	12 mA Max.	28 mA Max.	20 mA Max.	OE=GND
Duty	CMOS level	t_w/t	40 % to 60 %	40 % to 60 %	1/2 V_{DD} level
	TTL level		45 % to 55 %		1.4 V level
Output voltage	V_{OH}	$V_{DD}-0.4$ V Min.	2.4 V Min.	$V_{DD}-0.4$ V Min.	$I_{OH} = -400 \mu A$ (P,PTJ) / -4 mA (PH)
	V_{OL}		0.4 V Max.		$I_{OL} = 16$ mA (P) / 8 mA (PTJ) / 4mA (PH)
Output load condition (fan out)	CMOS	C_L	50 pF Max.	50 pF Max.	
	TTL	N	10 TTL Max.	5 TTL Max.	$C_L \leq 15$ pF
Output enable/disable input voltage	V_{IH}	2.0 V Min.	3.5 V Min.	2.0 V Min.	$I_{IH} = 1 \mu A$ Max. (OE= V_{DD})
	V_{IL}	0.8 V Max.	1.5 V Max.	0.8 V Max.	$I_{IL} = -100 \mu A$ Min. (OE=GND), PTJ: $I_{IL} = -500 \mu A$ Min. (OE=GND)
Output rise time	CMOS level	t_{TLH}	8 ns Max.	7 ns Max.	CMOS load: 20 % \rightarrow 80 % V_{DD}
	TTL level		5 ns Max.	—	TTL load: 0.4 V \rightarrow 2.4 V
Output fall time	CMOS level	t_{THL}	8 ns Max.	7 ns Max.	CMOS load: 80 % \rightarrow 20 % V_{DD}
	TTL level		5 ns Max.	—	TTL load: 2.4 V \rightarrow 0.4 V
Oscillation start up time	t_{OSC}	4 ms Max.	10 ms Max.		More than for 1 ms until $V_{DD} = 0$ V \rightarrow 4.5 V Time at 4.5 V to be 0 s
Aging	f_a		$\pm 5 \times 10^{-6}$ /year Max.		$T_a = +25$ °C, $V_{DD} = 5$ V, first year
Shock resistance	S.R.		$\pm 20 \times 10^{-6}$ Max.		Three drops on a hard board from 750 mm or excitation test with 29400 m/s ² x 0.3 ms x 1/2 sine wave in 3 directions

Note: • Unless otherwise stated, characteristics (specifications) shown in the above table are based on the rated operating temperature and voltage condition.
• External by-pass capacitor is recommended.

External dimensions

(Unit: mm)



Specifications (characteristics)

Item	Symbol	Specifications		Remarks
		SG-531PCG	SG-531SCG	
Output frequency range	fo	1.5000 MHz to 26.0000 MHz		Refer to page 31. "Frequency range"
Power source voltage	Max. supply voltage	V _{DD-GND}	-0.5 V to +7.0 V	
	Operating voltage	V _{DD}	2.7 V to 3.6 V	
Temperature range	Storage temperature	T _{STG}	-55 °C to +125 °C	Stored as bare product after unpacking
	Operating temperature	T _{OPR}	-40 °C to +85 °C	Refer to page 31. "Frequency range"
Frequency stability	Δf/fo	B : ±50 x 10 ⁻⁶ C : ±100 x 10 ⁻⁶		-20 °C to +70 °C
		M : ±100 x 10 ⁻⁶		-40 °C to +85 °C
Current consumption	I _{OP}	12 mA Max.		No load condition
Output disable current	I _{OE}	10 mA Max.	—	OE=GND (PCG)
Standby current	I _{ST}	—	50 μA Max.	ST=GND (SCG)
Duty	tw/t	45 % to 55 %		50 % V _{DD} , CL = 25 pF
Output voltage	V _{OH}	V _{DD} -0.4 V Min.		I _{OH} = -8 mA
	V _{OL}	0.4 V Max.		I _{OL} = 8 mA
Output load condition (fan out)	CL	25 pF		
Output enable disable input voltage	V _{IH}	70 % V _{DD} Min.		OE, ST
	V _{IL}	20 % V _{DD} Max.		OE, ST
Output rise time	t _{TLH}	4.0 ns Max.		20 % to 80 % V _{DD} , CL ≤ 25 pF
Output fall time	t _{THL}	4.0 ns Max.		80 % to 20 % V _{DD} CL ≤ 25 pF
Oscillation start up time	t _{OSC}	12 ms Max.		Time at minimum operating voltage to be 0 s
Aging	fa	±5 x 10 ⁻⁶ / year Max.		Ta=+25 °C, V _{DD} =3.3 V, First year
Shock resistance	S.R.	±20 x 10 ⁻⁶ Max.		Three drops on a hard board from 750 mm or excitation test with 29400 m/s ² x 0.3 ms x 1/2 sine wave in 3 directions

Specifications (characteristics)

Item	Symbol	Specifications			Remarks
		SG-531PTW/STW	SG-531PHW/SHW	SG-531PCW/SCW	
Output frequency range	fo	55.0001 MHz to 135.0000 MHz		26.0001 MHz to 135.0000 MHz	Refer to page 31. "Frequency range"
Power source voltage	Max. supply voltage	V _{DD-GND}	-0.5 V to +7.0 V		
	Operating voltage	V _{DD}	5.0 V ± 0.5 V	3.3 V ± 0.3 V	
Temperature range	Storage temperature	T _{STG}	-55 °C to +100 °C		Stored as bare product after unpacking
	Operating temperature	T _{OPR}	-20 °C to +70 °C	-40 °C to +85 °C	Refer to page 31. "Frequency range"
Frequency stability	Δf/fo	B : ±50 x 10 ⁻⁶ C : ±100 x 10 ⁻⁶			-20 °C to +70 °C
		—			M : ±100 x 10 ⁻⁶
Current consumption	I _{OP}	45 mA Max.		28 mA Max.	No load condition
Output disable current	I _{OE}	30 mA Max.		16 mA Max.	OE=GND(P*W)
Standby current	I _{ST}	50 μA Max.		—	ST=GND(S*W)
Duty	tw/t	40 % to 60 %	—	—	TTL load : 1.4 V, CL = Max.
		45 % to 55 %	—	—	TTL load : 1.4 V, 5TTL + 15 pF, fo ≤ 66.6667 MHz
		—	40 % to 60 %	40 % to 60 %	CMOS load : 50% V _{DD} , CL = Max.
		—	45 % to 55 %	—	CMOS load : 50% V _{DD} , CL = 25 pF, fo ≤ 66.6667 MHz
Output voltage	V _{OH}	V _{DD} -0.4 V Min.		I _{OH} = -16 mA (*TW/*HW)/-8 mA(*CW)	
	V _{OL}	0.4 V Max.		I _{OL} = 16 mA (*TW/*HW)/8 mA(*CW)	
Output load condition (fan out)	CL	15 pF	—	—	fo ≤ 135 MHz
		5 TTL + 15 pF	—	—	fo ≤ 90 MHz
		25 pF	—	—	fo ≤ 66.6667 MHz
		—	15 pF	15 pF	fo ≤ 135 MHz
		—	25 pF	—	fo ≤ 125 MHz
Output enable disable input voltage	V _{IH}	2.0 V Min.		0.7 V _{DD} Min.	OE, ST
	V _{IL}	0.8 V Max.		0.2 V _{DD} Max.	OE, ST
Output rise time	t _{TLH}	2.0 ns Max.	—	—	TTL load: 0.8 V→2.0 V, CL = Max.
		4.0 ns Max.	—	—	TTL load: 0.4 V→2.4 V, CL = Max.
		—	3.0 ns Max.	—	CMOS load: 20 %→80 % V _{DD} , CL= 25 pF
		—	—	3.0 ns Max.	CMOS load: 20 %→80 % V _{DD} , CL= 15 pF
Output fall time	t _{THL}	—	4.0 ns Max.	4.0 ns Max.	CMOS load: 20 %→80 % V _{DD} , CL= Max.
		2.0 ns Max.	—	—	TTL load: 2.0 V→0.8 V, CL = Max.
		4.0 ns Max.	—	—	TTL load: 2.4 V→0.4 V, CL = Max.
		—	3.0 ns Max.	—	CMOS load: 80 %→20 % V _{DD} , CL= 25 pF
Oscillation start up time	t _{OSC}	—	—	3.0 ns Max.	CMOS load: 80 %→20 % V _{DD} , CL= 15 pF
		—	4.0 ns Max.	4.0 ns Max.	CMOS load: 80 %→20 % V _{DD} , CL= Max.
Oscillation start up time	t _{OSC}	10 ms Max.		Time at minimum operating voltage to be 0 s	
Aging	fa	±5 x 10 ⁻⁶ / year Max.		Ta=+25 °C, V _{DD} =5.0 V / 3.3 V, First year	
Shock resistance	S.R.	±20 x 10 ⁻⁶ Max.		Three drops on a hard board from 750 mm or excitation test with 29400 m/s ² x 0.3 ms x 1/2 sine wave in 3 directions	